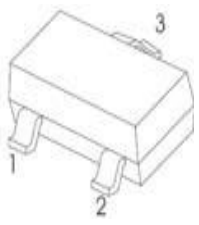
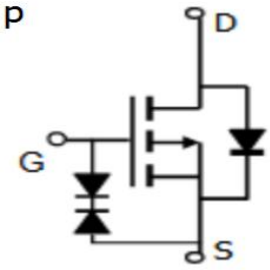
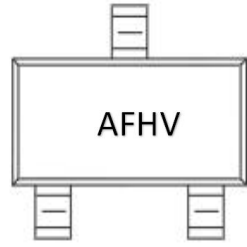
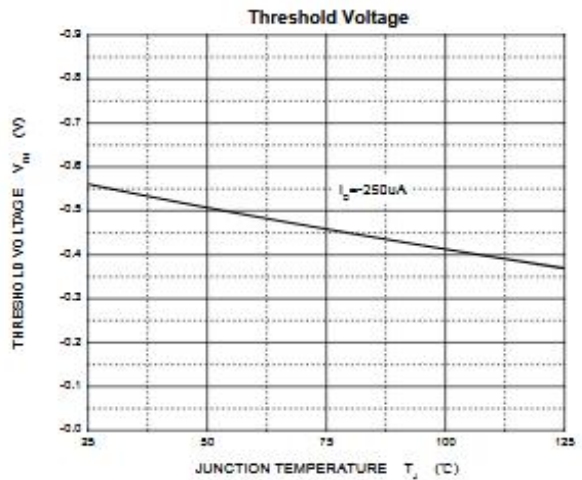
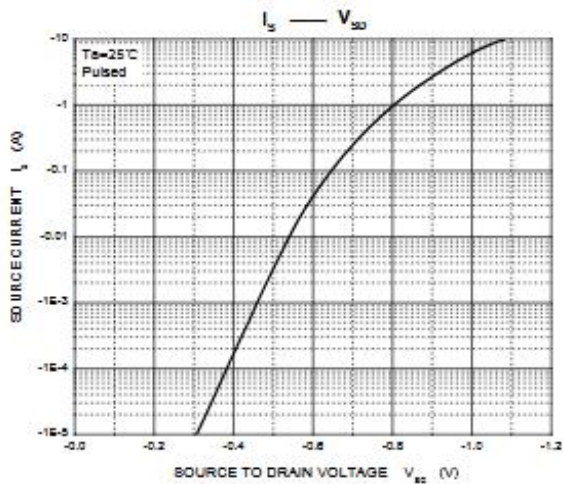
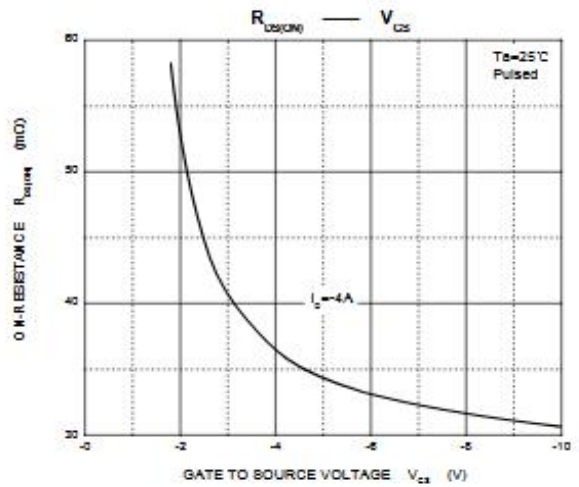
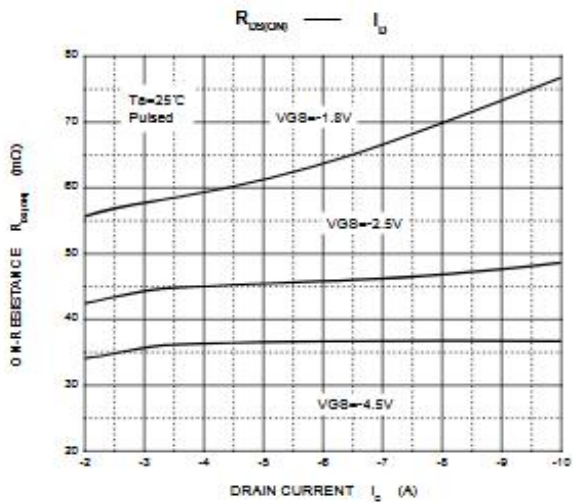
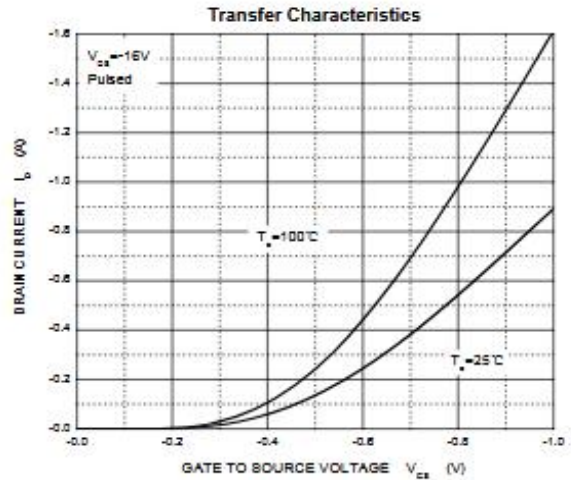
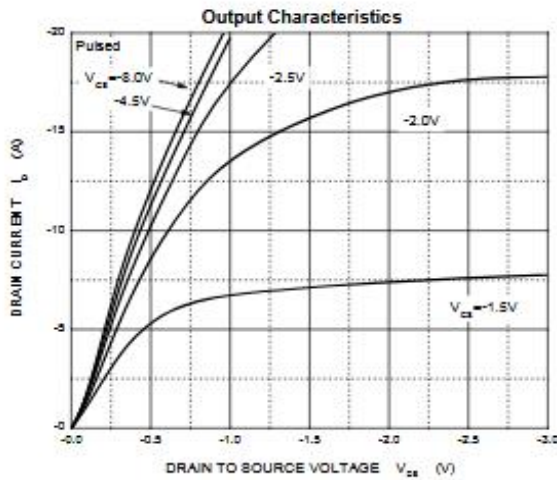


<b>P-Channel 20-V(D-S) MOSFET</b>		<b>SOT-23 Plastic-Encapsulate MOSFETS</b>	
<p><b>SOT-23</b></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p><b>Equivalent Circuit</b></p> 		<p><b>Features</b></p> <ul style="list-style-type: none"> <li>※ TrenchFET Power MOSFET</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>※ Load Switch for Portable Devices</li> <li>※ DC/DC Converter</li> </ul> <p><b>MARKING</b></p> 	
<b>V(BR)DSS</b>	<b>RDS(on)MAX</b>	<b>ID</b>	
-20 V	47m Ω @-4.5V	-4A	
	60m Ω @-2.5V		
<b>Maximum ratings ( Ta=25°C unless otherwise noted)</b>			
<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	±8	
Continuous Drain Current	ID	-4	A
Pulsed Diode Curren	IDM	-30	
Power Dissipation	PD	0.35	W
Thermal Resistance from Junction to Ambient (t≤5s)	R θ JA	150	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	

<b>MOSFET ELECTRICAL CHARACTERISTICS</b>						
<b>Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)</b>						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250µA	-20			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = -250µA	-0.4	-0.7	-1	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -20V, VGS =0V			-1	µA
Drain-source on-state resistancea	RDS(on)	VGS = -10V, ID = -4A		37	47	mΩ
		VGS = -4.5V, ID = -4A		48	60	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -4A	7			S
Diode forward voltage	VSD	IS=1A,VGS=0V		-0.8	-1.3	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = -8V,VGS =0V, f=1MHz		1450		pF
Output capacitance	Coss			205		pF
Reverse transfer capacitanceb	Crss			160		pF
Total gate charge	Qg	VDS = -20V,VGS = -4.5V, ID =-4.5A		17.2		nC
Gate-source charge	Qgs			1.3		nC
Gate-drain charge	Qgd			4.5		nC
Gate resistance	Rg	f=1MHz		6.5		Ω
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDD= -10V RL=10Ω, ID ≈ -1A, VGEN=- 4.5V,Rg=6Ω		9.5		ns
Rise time	tr			17		ns
Turn-off delay time	td(off)			94		ns
Fall time	tf			35		ns
<p><b>Note :</b></p> <ol style="list-style-type: none"> <li>1. Repetitive Rating : Pulse width limited by maximum junction temperature.</li> <li>2. Surface Mounted on FR4 Board, t &lt; 5 sec.</li> <li>3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.</li> <li>4. Guaranteed by design, not subject to production testing.</li> </ol>						

**Typical Characteristics:**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)